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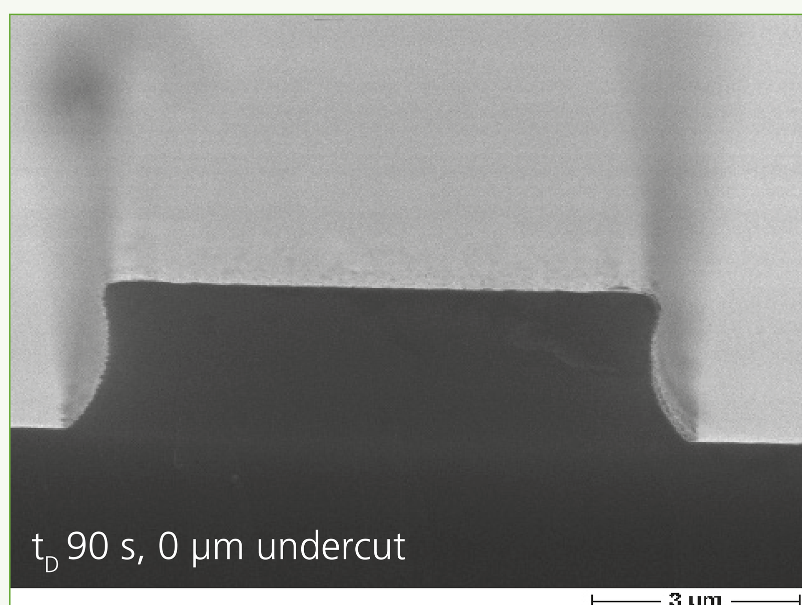
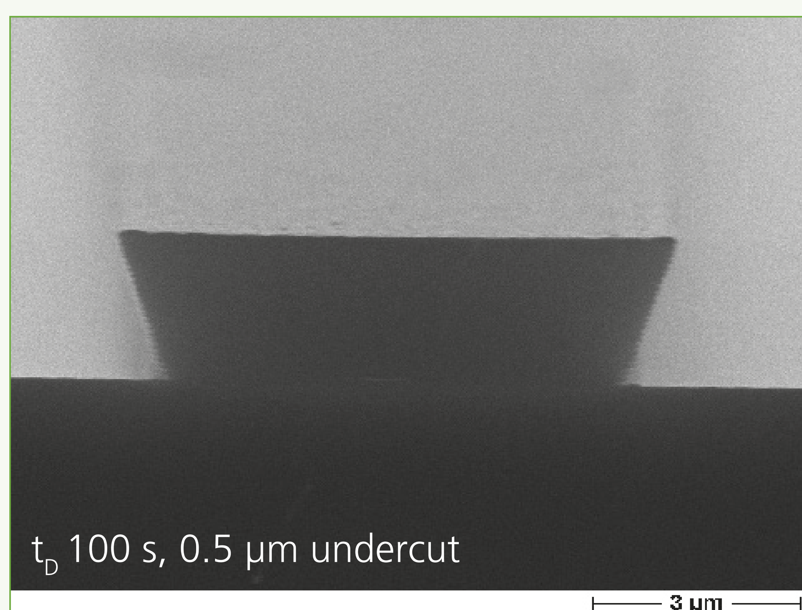
micro resist technology

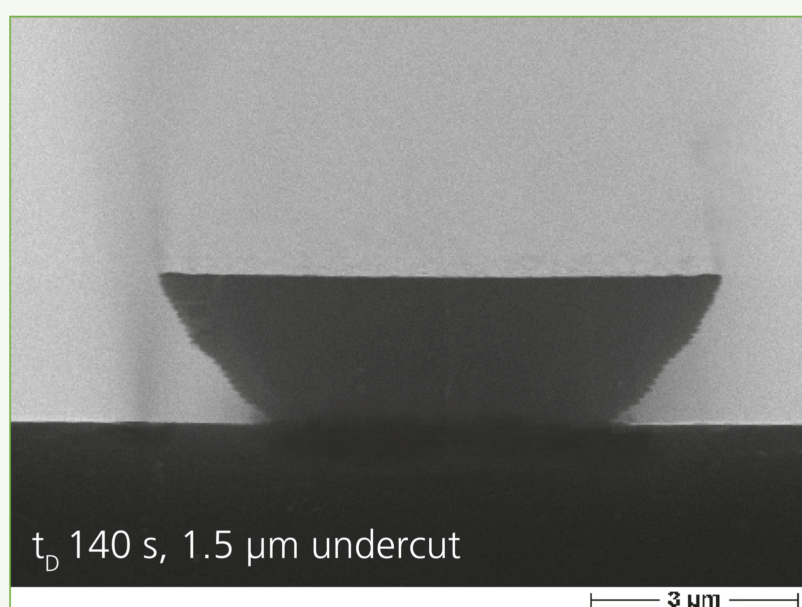
ma-N 400 and ma-N 1400 - Negative Tone Photoresists

Conventional Pattern Transfer and Single-Layer Lift-Off

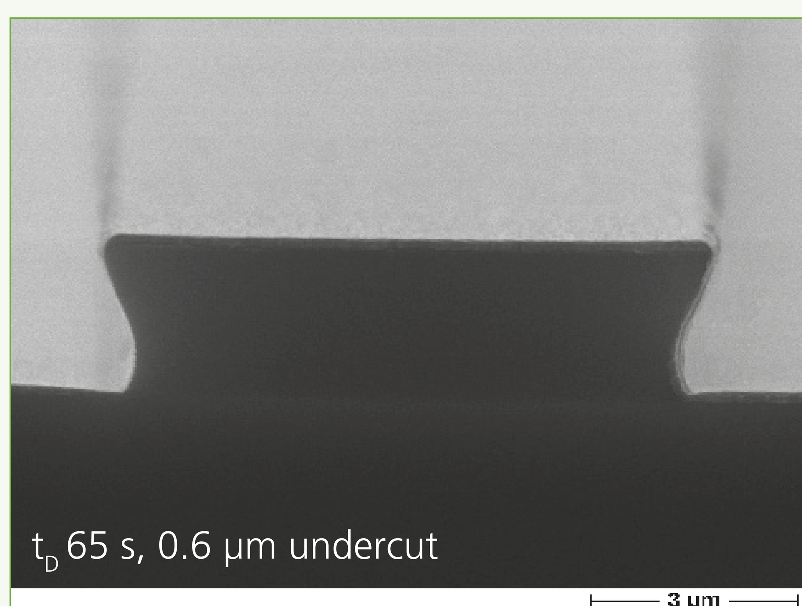
ma-N 400, 2 µm thick

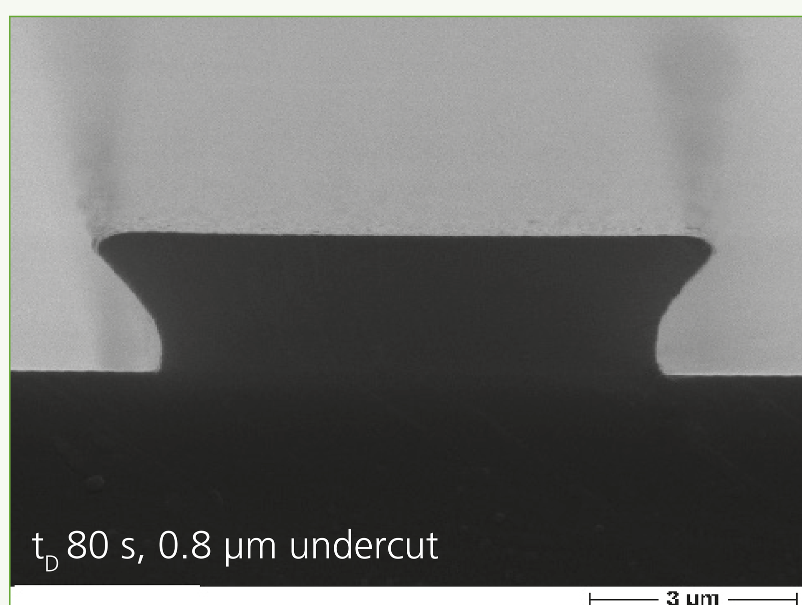


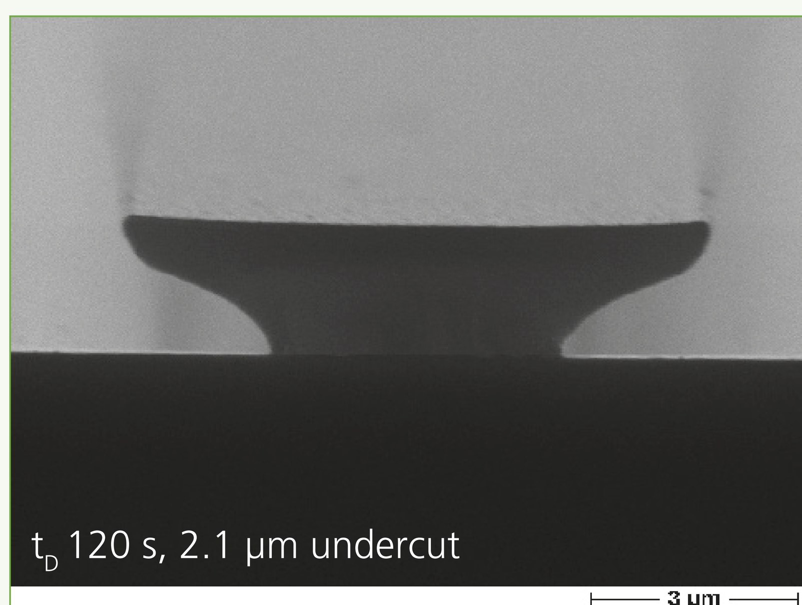




ma-N 1400, 2 µm thick







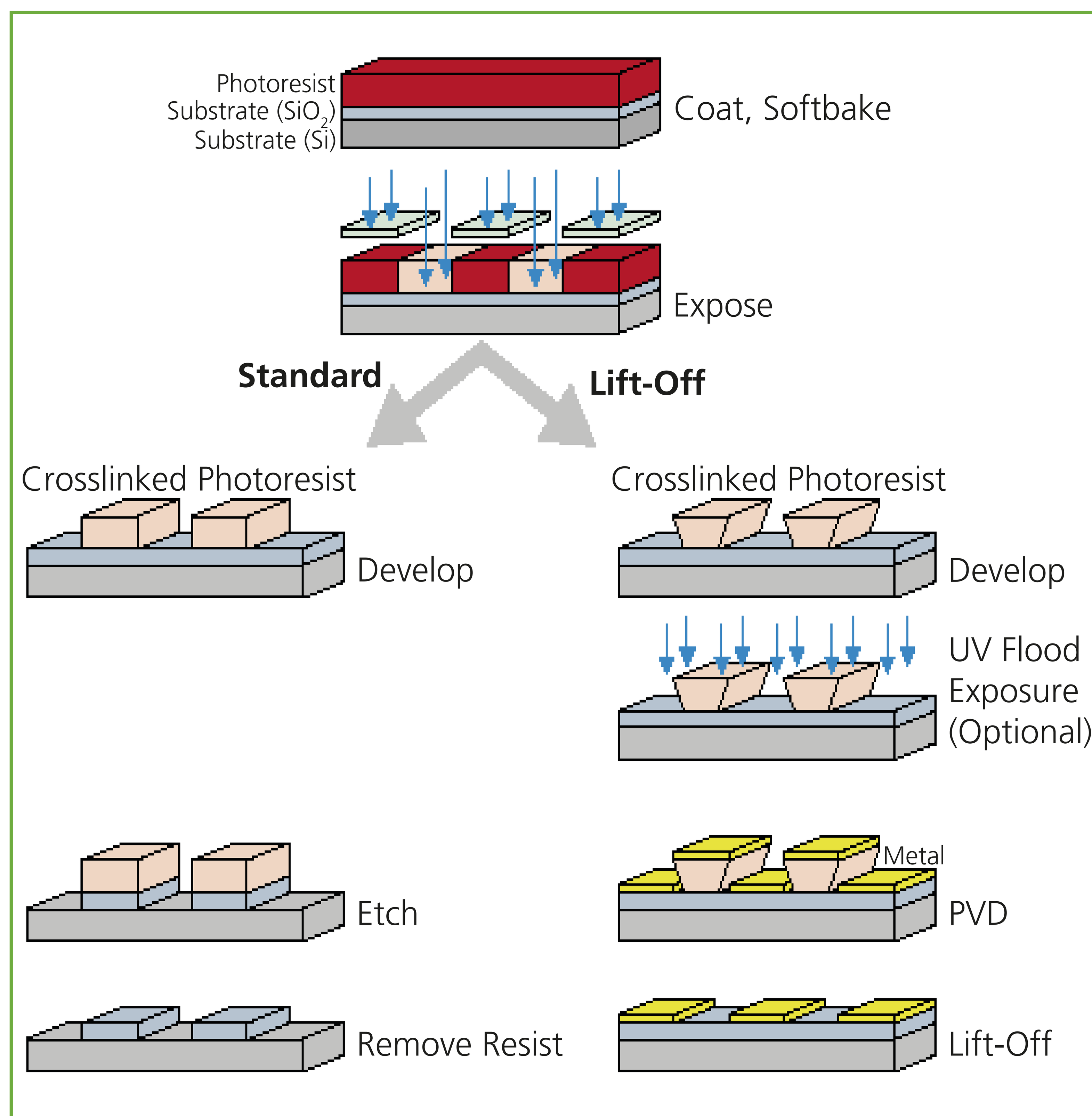
Unique features

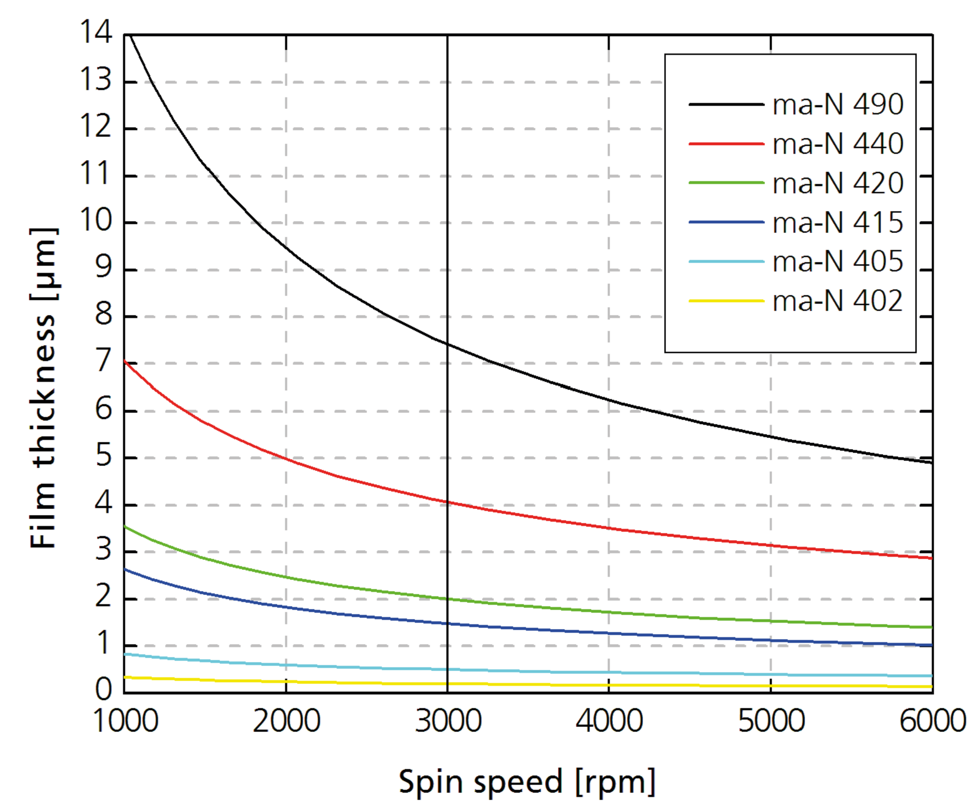
- High wet and dry etch resistance
- Good thermal stability of the resist pattern
- Tunable pattern profile: vertical to undercut
- Aqueous alkaline development
- Easy to remove
- Resists available in a variety of viscosities

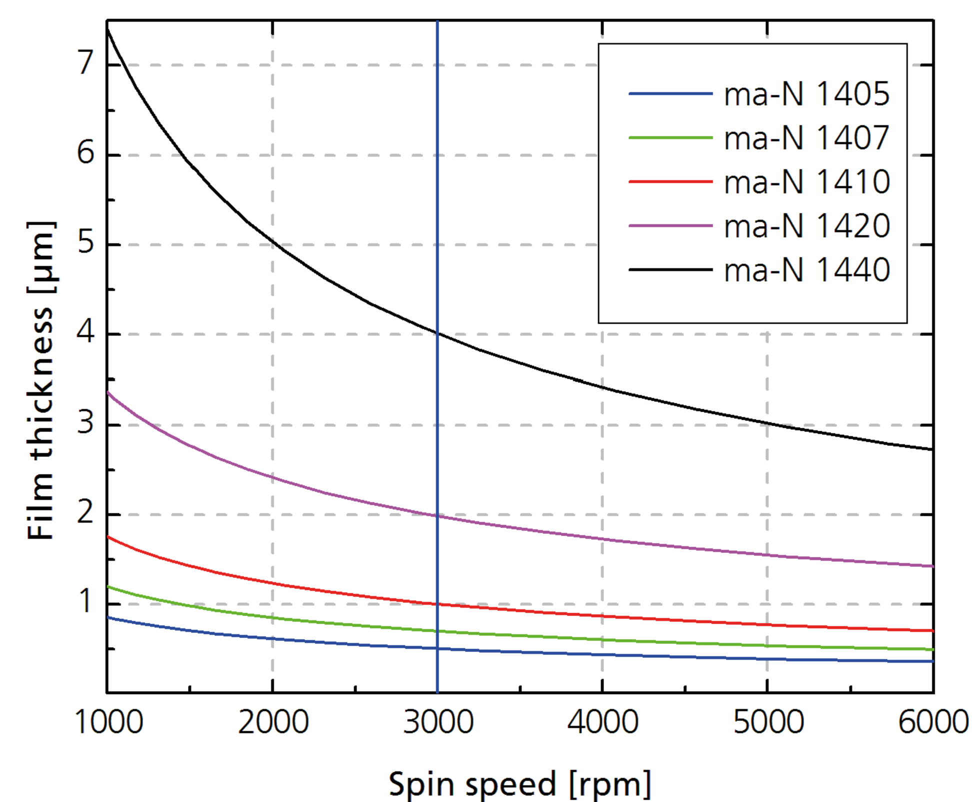
Applications

- Microelectronics and micro systems technology
- Mask for lift-off processes
- Etch mask for semiconductors and metals
- Well suitable for implantation

Standard and Lift-off process flow







Technical data

Resist	ma-N 400	µm	ma-N 1400	µm
Film thickness	ma-N 402	0.2		
	ma-N 405	0.5	ma-N 1405	0.5
	ma-N 415	1.5	ma-N 1407	0.7
	ma-N 420	2.0	ma-N 1410	1.0
	ma-N 440	4.1	ma-N 1420	2.0
	ma-N 490	7.5	ma-N 1440	4.0
Spin coating	3000 rpm; 30 s			
Spectral sensitivity	300 - 380 nm		300 - 410 nm	
Thermal stability	Up to 110 °C, for metal evaporation		Up to 160 °C, for metal evaporation and sputtering